

PROTECTION PRODUCTS
Description

The SM series of transient voltage suppressors (TVS) are designed to protect components which are connected to data and transmission lines from voltage surges caused by **ESD** (electrostatic discharge), **EFT** (electrical fast transients), and **lightning**.

TVS diodes are characterized by their high surge capability, low operating and clamping voltages, and fast response time. This makes them ideal for use as board level protection of sensitive semiconductor components. The dual-junction common-anode design allows the user to protect one bidirectional data line or two unidirectional lines. The low profile SOT23 package allows flexibility in the design of "crowded" circuit boards.

The SM series will meet the surge requirements of IEC 61000-4-2 (Formerly IEC 801-2), Level 4, "Human Body Model" for air and contact discharge.

Features

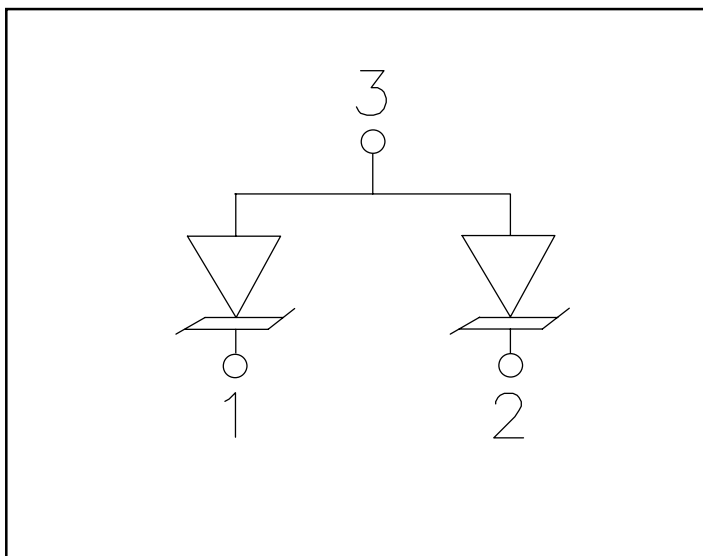
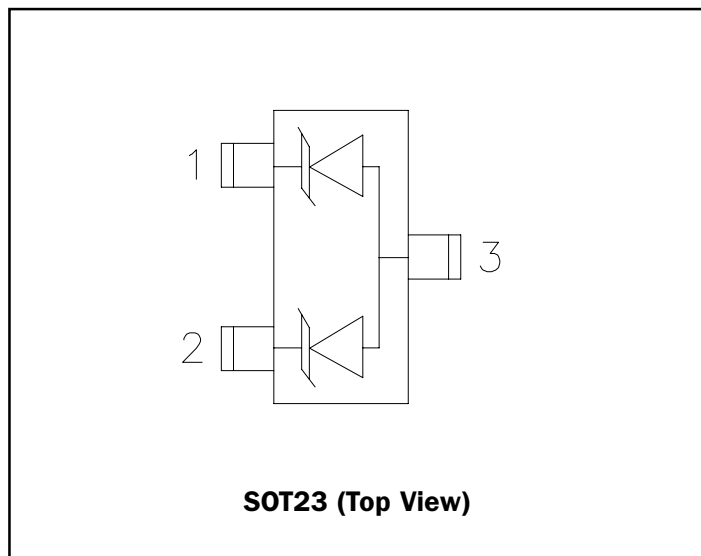
- ◆ 300 watts peak pulse power ($t_p = 8/20\mu s$)
- ◆ Transient protection for data & power lines to **IEC 61000-4-2 (ESD) 15kV (air), 8kV (contact)**
IEC 61000-4-4 (EFT) 40A ($t_p=5/50ns$)
IEC 61000-4-5 (Lightning) 12A ($t_p=1.2/50\mu s$)
- ◆ Protects one bidirectional line or two unidirectional lines
- ◆ Working Voltages: 5V, 12V, 15V, 24 and 36V
- ◆ Low clamping voltage
- ◆ Solid-state silicon avalanche technology

Mechanical Characteristics

- ◆ JEDEC SOT23 package
- ◆ Molding compound flammability rating: UL 94V-0
- ◆ Marking : Marking Code
- ◆ Packaging : Tape and Reel per EIA 481

Applications

- ◆ Cellular Handsets and Accessories
- ◆ Portable Electronics
- ◆ Industrial Controls
- ◆ Set-Top Box
- ◆ Servers, Notebook, and Desktop PC

Circuit Diagram

Schematic & PIN Configuration


PROTECTION PRODUCTS

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (tp = 8/20μs)	P _{pk}	300	Watts
Thermal Resistance, Junction to Ambient	θ _{JA}	556	°C/W
Lead Soldering Temperature	T _L	260 (10 sec.)	°C
Operating Temperature	T _J	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics

SM05						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}				5	V
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA	6			V
Reverse Leakage Current	I _R	V _{RWM} = 5V, T=25°C			20	μA
Clamping Voltage	V _C	I _{pp} = 1A, tp = 8/20μs			9.8	V
Maximum Peak Pulse Current	I _{pp}	tp = 8/20μs			17	A
Junction Capacitance	C _j	Pin 1 to 2 V _R = 0V, f = 1MHz			350	pF
Junction Capacitance	C _j	Pin 1 to 3 and Pin 2 to 3 V _R = 0V, f = 1MHz			400	pF

SM12						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V _{RWM}				12	V
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA	13.3			V
Reverse Leakage Current	I _R	V _{RWM} = 12V, T=25°C			1	μA
Clamping Voltage	V _C	I _{pp} = 1A, tp = 8/20μs			19	V
Maximum Peak Pulse Current	I _{pp}	tp = 8/20μs			12	A
Junction Capacitance	C _j	Pin 1 to 2 V _R = 0V, f = 1MHz			120	pF
Junction Capacitance	C _j	Pin 1 to 3 and Pin 2 to 3 V _R = 0V, f = 1MHz			150	pF

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Electrical Characteristics (Continued)

SM15						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				15	V
Reverse Breakdown Voltage	V_{BR}	$I_t = 1\text{mA}$	16.7			V
Reverse Leakage Current	I_R	$V_{RWM} = 15\text{V}, T=25^\circ\text{C}$			1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			24	V
Maximum Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$			10	A
Junction Capacitance	C_j	Pin 1 to 2 $V_R = 0\text{V}, f = 1\text{MHz}$			75	pF
Junction Capacitance	C_j	Pin 1 to 3 and 2 to 3 $V_R = 0\text{V}, f = 1\text{MHz}$			100	pF

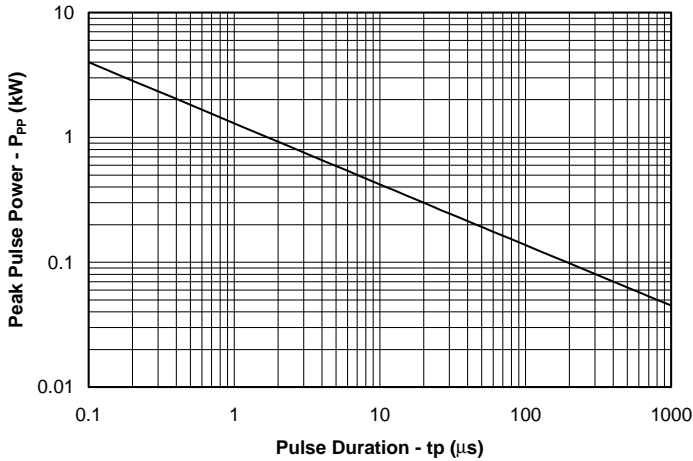
SM24						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				24	V
Reverse Breakdown Voltage	V_{BR}	$I_t = 1\text{mA}$	26.7			V
Reverse Leakage Current	I_R	$V_{RWM} = 24\text{V}, T=25^\circ\text{C}$			1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			43	V
Maximum Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$			5	A
Junction Capacitance	C_j	Pin 1 to 2 $V_R = 0\text{V}, f = 1\text{MHz}$			50	pF
Junction Capacitance	C_j	Pin 1 to 3 and 2 to 3 $V_R = 0\text{V}, f = 1\text{MHz}$			60	pF

SM36						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				36	V
Reverse Breakdown Voltage	V_{BR}	$I_t = 1\text{mA}$	40			V
Reverse Leakage Current	I_R	$V_{RWM} = 36\text{V}, T=25^\circ\text{C}$			1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			60	V
Maximum Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$			4	A
Junction Capacitance	C_j	Pin 1 to 2 $V_R = 0\text{V}, f = 1\text{MHz}$			40	pF
Junction Capacitance	C_j	Pin 1 to 3 and 2 to 3 $V_R = 0\text{V}, f = 1\text{MHz}$			45	pF

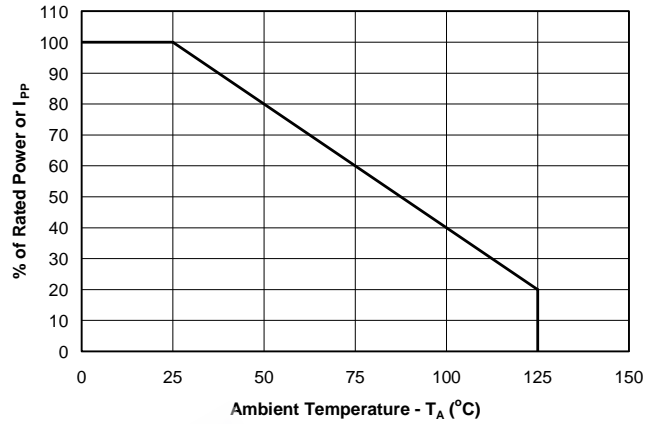
PROTECTION PRODUCTS

Typical Characteristics

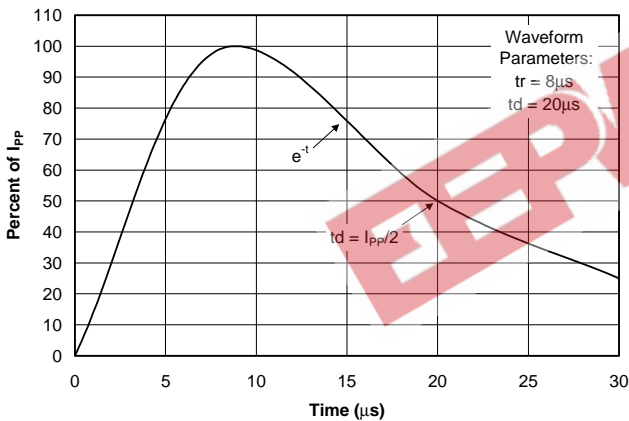
Non-Repetitive Peak Pulse Power vs. Pulse Time



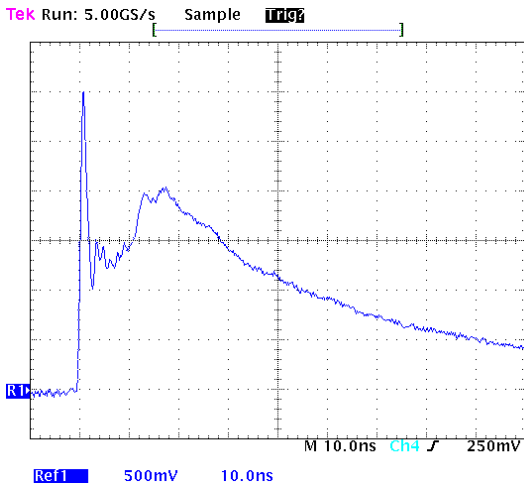
Power Derating Curve



Pulse Waveform



ESD Pulse Waveform (Per IEC 61000-4-2)



IEC 61000-4-2 Discharge Parameters

Level	First Peak Current (A)	Peak Current at 30 ns (A)	Peak Current at 60 ns (A)	Test Voltage (Contact Discharge) (kV)	Test Voltage (Air Discharge) (kV)
1	7.5	4	8	2	2
2	15	8	4	4	4
3	22.5	12	6	6	8
4	30	16	8	8	15

PROTECTION PRODUCTS
Applications Information
Device Connection Options

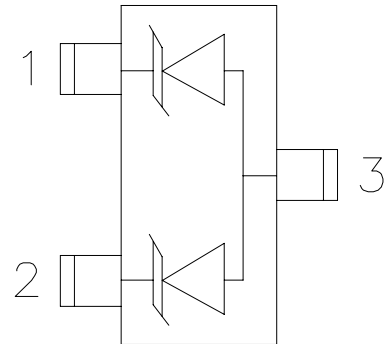
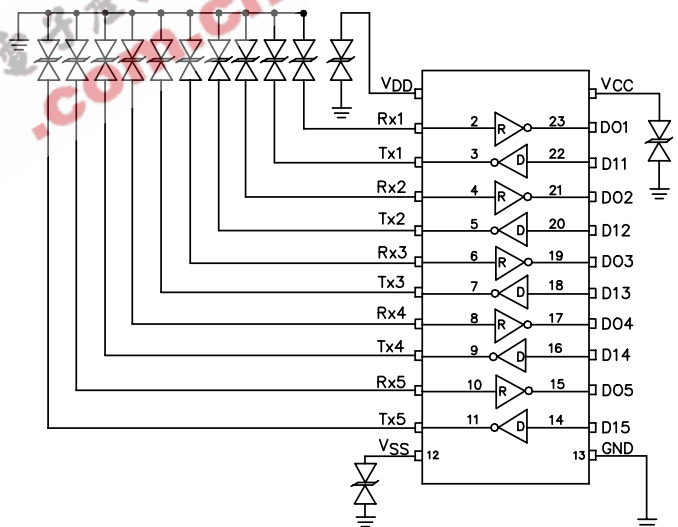
The SM series is designed to protect one bidirectional or two unidirectional data or I/O lines operating at 5 to 36 volts. Connection options are as follows:

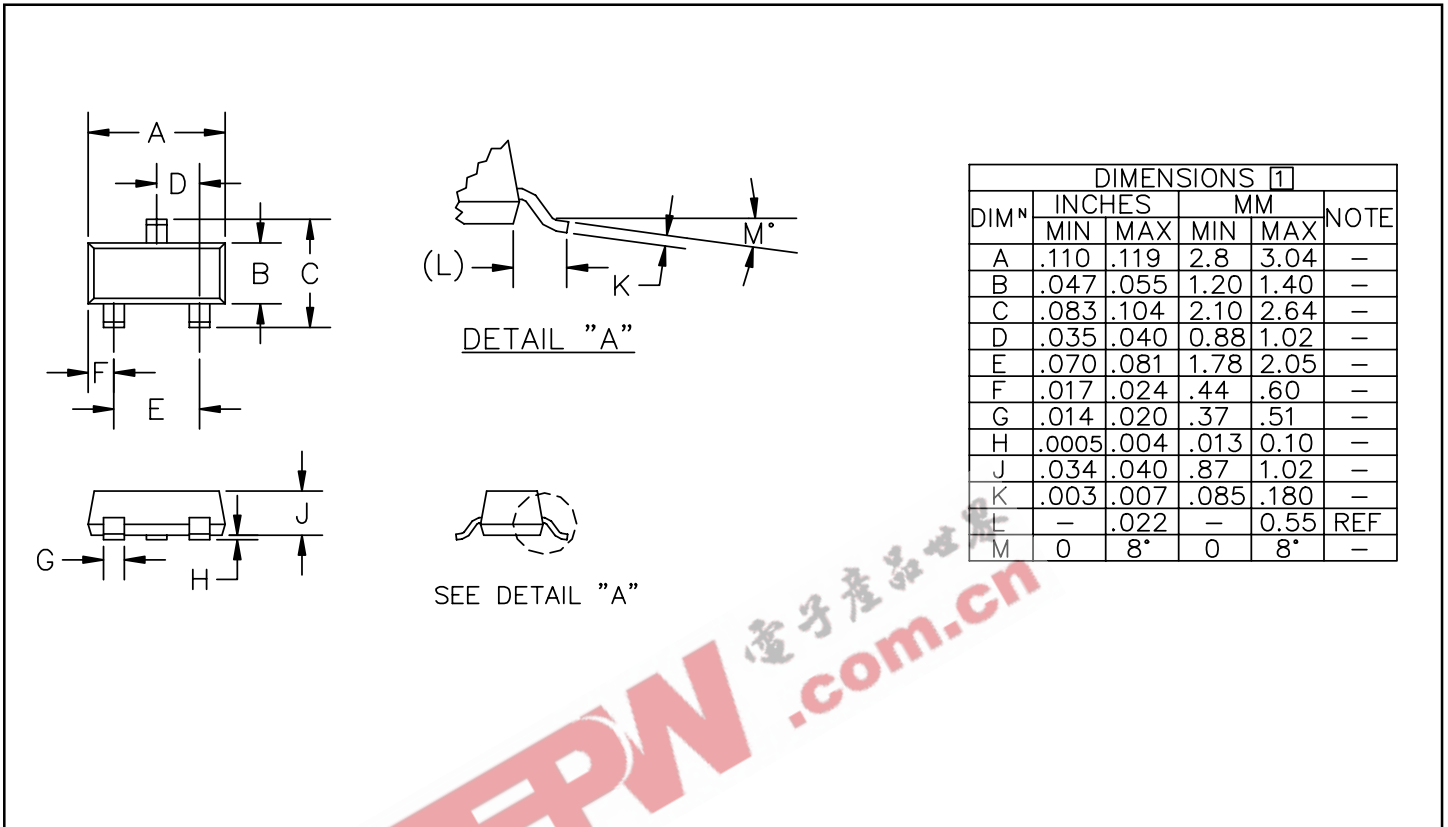
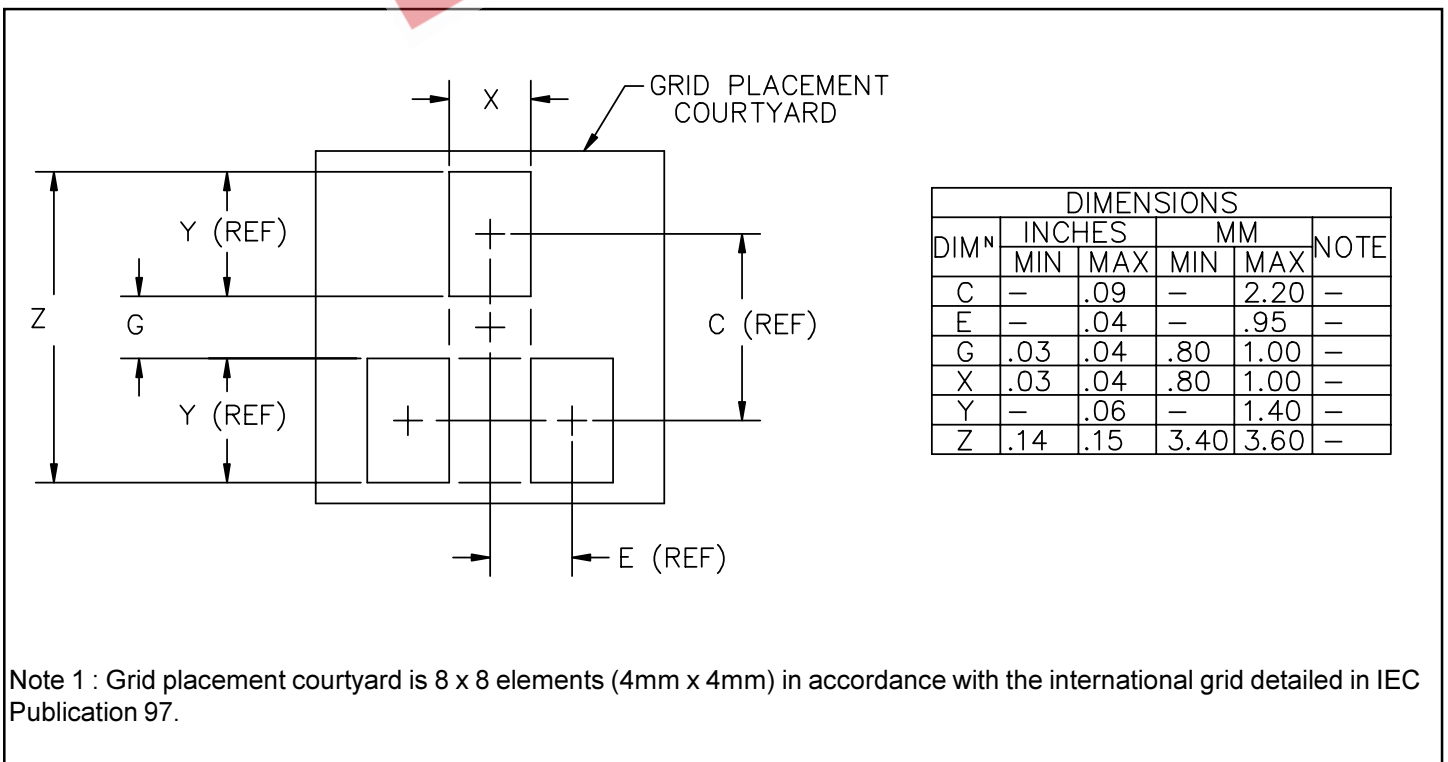
- **Bidirectional:** Pin 1 is connected to the data line and pin 2 is connected to ground (Since the device is symmetrical, these connections may be reversed). For best results, the ground connection should be made directly to a ground plane on the board. The path length should be kept as short as possible to minimize parasitic inductance. Pin 3 is not connected.
- **Unidirectional:** Data lines are connected to pin 1 and pin 2. Pin 3 is connected to ground. For best results, this pin should be connected directly to a ground plane on the board. The path length should be kept as short as possible to minimize parasitic inductance.

Circuit Board Layout Recommendations for Suppression of ESD.

Good circuit board layout is critical for the suppression of fast rise-time transients such as ESD. The following guidelines are recommended (Refer to application note SI99-01 for more detailed information):

- Place the TVS near the input terminals or connectors to restrict transient coupling.
- Minimize the path length between the TVS and the protected line.
- Minimize all conductive loops including power and ground loops.
- The ESD transient return path to ground should be kept as short as possible.
- Never run critical signals near board edges.
- Use ground planes whenever possible.

Device Schematic & Pin Configuration

RS-232 Transceiver Protection Example


PROTECTION PRODUCTS
Outline Drawing - SOT23

Land Pattern - SOT23


PROTECTION PRODUCTS

Marking Codes

Part Number	Marking Code
SM05	M05
SM12	M12
SM15	M15
SM24	M24
SM36	M36

Ordering Information

Part Number	Working Voltage	Qty per Reel	Reel Size
SM05.TC	5V	3,000	7 Inch
SM05.TG	5V	10,000	13 Inch
SM12.TC	12V	3,000	7 Inch
SM12.TG	12V	10,000	13 Inch
SM15.TC	15V	3,000	7 Inch
SM15.TG	15V	10,000	13 Inch
SM24.TC	24V	3,000	7 Inch
SM24.TG	24V	10,000	13 Inch
SM36.TC	36V	3,000	7 Inch

Contact Information

Semtech Corporation
 Protection Products Division
 652 Mitchell Rd., Newbury Park, CA 91320
 Phone: (805)498-2111 FAX (805)498-3804